



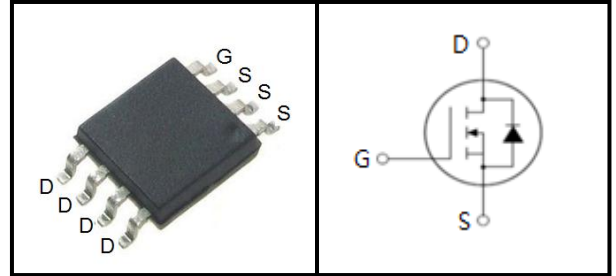
100V N-Channel DTMOS

FEATURES

- Trench Power DTMOS technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Optimized for fast-switching applications

APPLICATIONS

- Synchronous Rectification in DC/DC and AC/DC Converters
- Isolated DC/DC Converters in Telecom and Industrial



Device Marking and Package Information		
Device	Package	Marking
TSJ10N10AT	SOP-8	10N10AT

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted			
Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS} = 0\text{V}$)	V_{DSS}	100	V
Continuous Drain Current	I_D	8	A
Pulsed Drain Current (note1)	I_{DM}	32	A
Gate-Source Voltage	V_{GSS}	± 20	V
Single Pulse Avalanche Energy (note2)	E_{AS}	10	mJ
Avalanche Current (note1)	I_{AS}	14	A
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	3.1	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ\text{C}$

Thermal Resistance			
Parameter	Symbol	Value	Unit
Junction-to-Drain Lead	R_{thJC}	24	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	40	



Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted								
Parameter	Symbol	Test Conditions	Value			Unit		
			Min.	Typ.	Max.			
Static								
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100	--	--	V		
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 95V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	μA		
		$V_{DS} = 95V, V_{GS} = 0V, T_J = 150^\circ\text{C}$	--	--	100			
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20V$	--	--	± 100	nA		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.1	--	2.5	V		
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 8A$	--	19	23	m Ω		
		$V_{GS} = 4.5V, I_D = 6A$	--	23	33			
Forward Transconductance (Note3)	g_{fs}	$V_{DS} = 5V, I_D = 1A$	--	30	--	S		
Dynamic								
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 50V,$ $f = 1.0\text{MHz}$	--	1134	--	pF		
Output Capacitance	C_{oss}		--	92	--			
Reverse Transfer Capacitance	C_{rss}		--	10.3	--			
Total Gate Charge	$Q_g(10V)$	$V_{DD} = 50V, I_D = 8A,$ $V_{GS} = 10V$	--	21	--	nC		
	$Q_g(4.5V)$		--	11	--			
Gate-Source Charge	Q_{gs}		--	3.1	--			
Gate-Drain Charge	Q_{gd}		--	5.1	--			
Turn-on Delay Time	$t_{d(on)}$		$V_{DD} = 50V, I_D = 8A,$ $R_G = 3\Omega$	--	7		--	ns
Turn-on Rise Time	t_r			--	3		--	
Turn-off Delay Time	$t_{d(off)}$	--		20	--			
Turn-off Fall Time	t_f	--		3	--			
Drain-Source Body Diode Characteristics								
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	4	A		
Pulsed Diode Forward Current	I_{SM}		--	--	12			
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = 1A, V_{GS} = 0V$	--	0.72	1	V		
Reverse Recovery Time	t_{rr}	$I_F = 8A,$ $di_F/dt = 500A/\mu s$	--	20	--	ns		
Reverse Recovery Charge	Q_{rr}		--	90	--	nC		

Notes

1. Repetitive Rating: Pulse Width limited by maximum junction temperature
2. $I_{AS} = 14A, V_{DD} = 50V, R_G = 25\Omega, \text{Starting } T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse Width $\leq 300\mu s, \text{Duty Cycle } \leq 1\%$
4. When mounted on 1" in square copper board



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

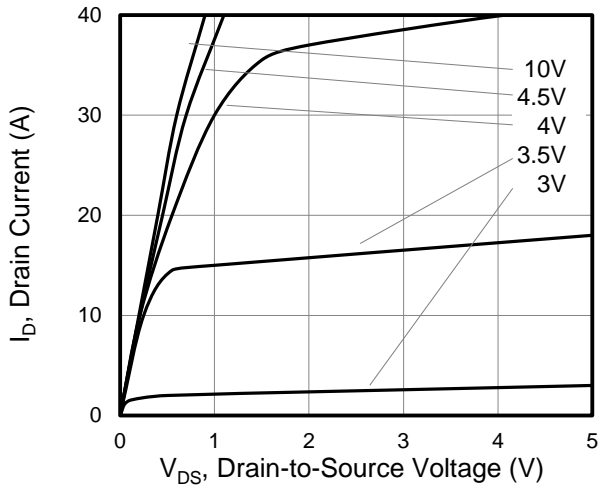


Figure 2. Transfer Characteristics

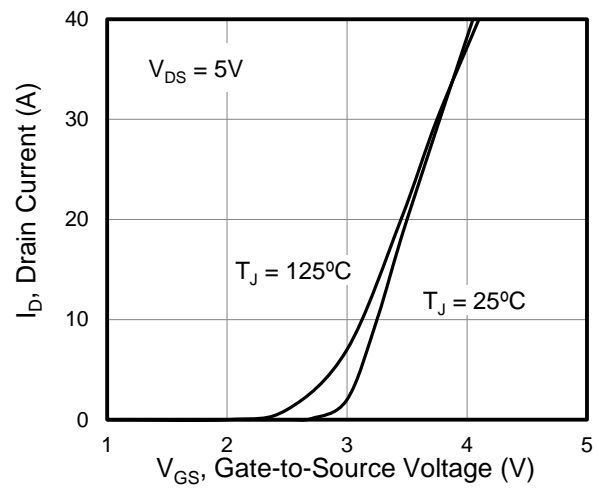


Figure 3. On-Resistance vs. Drain Current

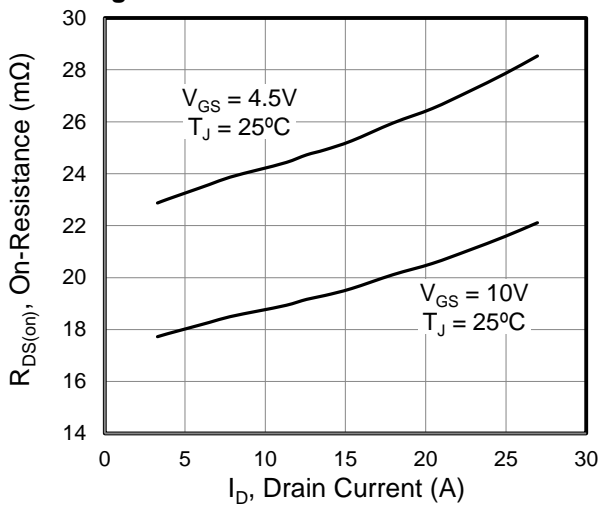


Figure 4. Capacitance

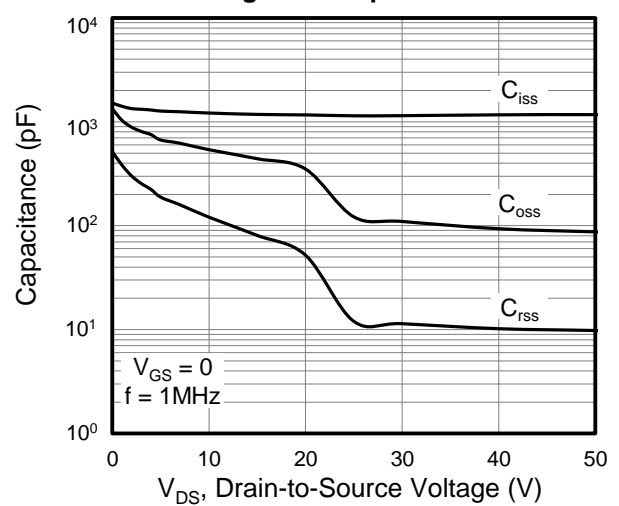


Figure 5. Gate Charge

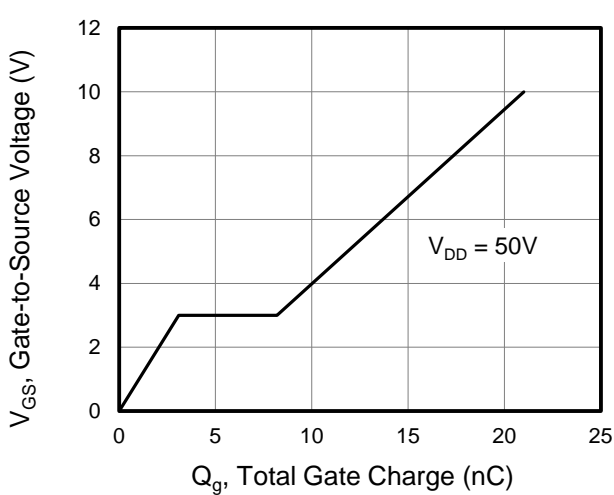
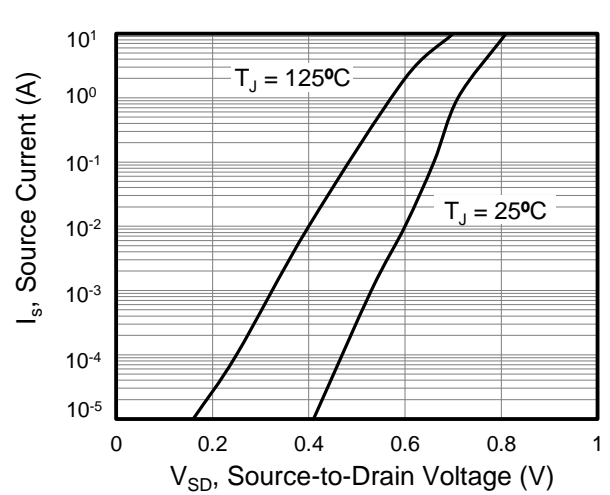


Figure 6. Body Diode Forward Voltage





Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. On-Resistance vs. Junction Temperature

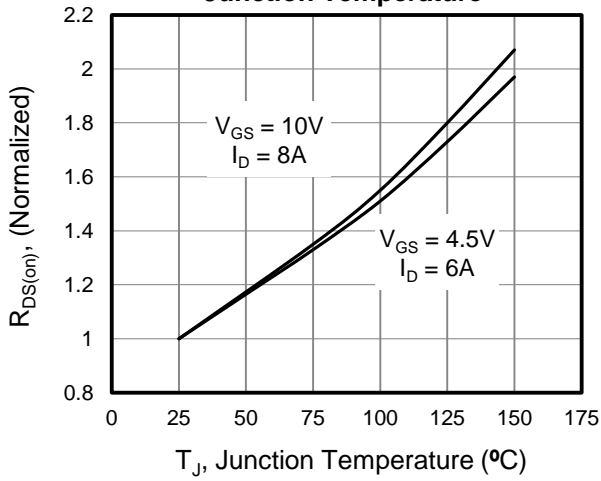


Figure 8. Threshold Voltage vs. Junction Temperature

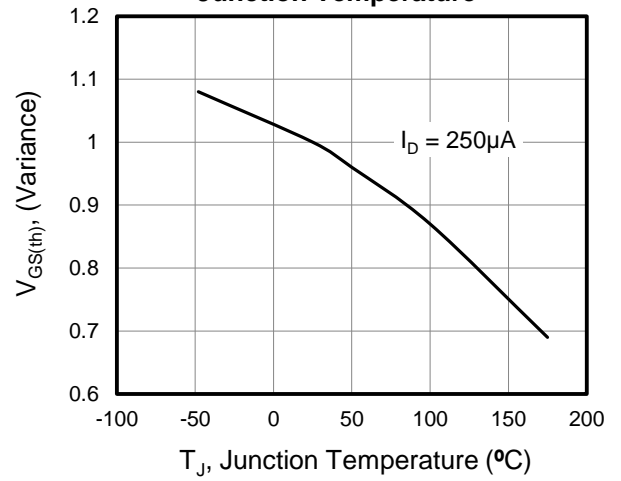


Figure 9. Transient Thermal Impedance

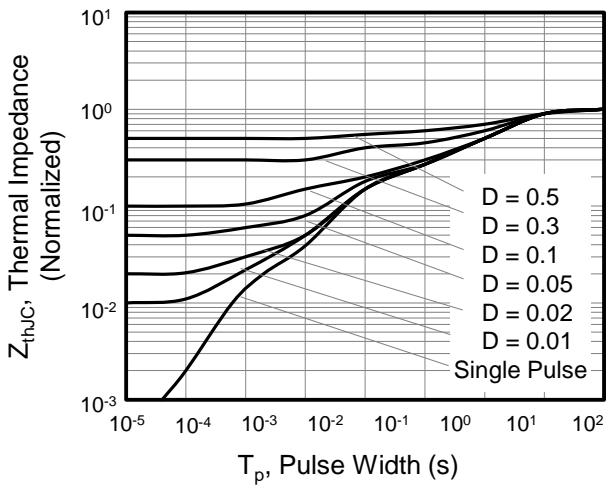




Figure A: Gate Charge Test Circuit and Waveform



Figure B: Resistive Switching Test Circuit and Waveform

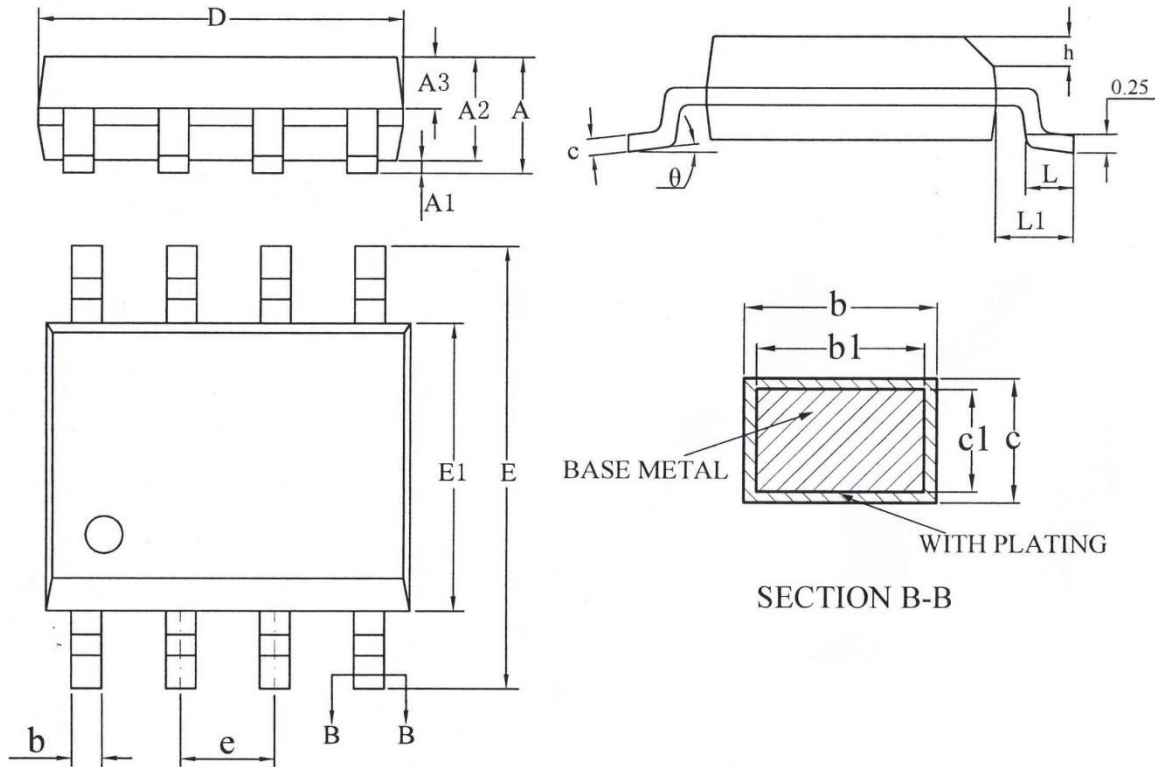


Figure C: Unclamped Inductive Switching Test Circuit and Waveform





SOP-8



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	—	—	1.75
A1	0.10	—	0.225
A2	1.30	1.40	1.50
A3	0.60	0.65	0.70
b	0.39	—	0.48
b1	0.38	0.41	0.43
c	0.21	—	0.26
c1	0.19	0.20	0.21

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	4.70	4.90	5.10
E	5.80	6.00	6.20
E1	3.70	3.90	4.10
e	1.27BSC		
h	0.25	—	0.50
L	0.50	—	0.80
L1	1.05BSC		
θ	0	—	8°



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